

# ESE535: Electronic Design Automation

Day 14: March 19, 2008  
Statistical Static Timing Analysis

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## Today

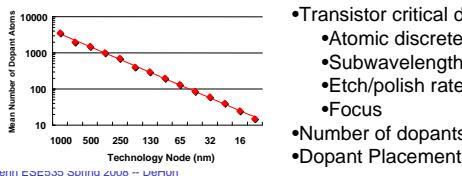
- Sources of Variation
- Limits of Worst Case
- Optimization for Parametric Yield
- Statistical Analysis
- Difficulties

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## Central Problem

- As our devices approach the atomic scale, we must deal with statistical effects governing the placement and behavior of individual atoms and electrons.



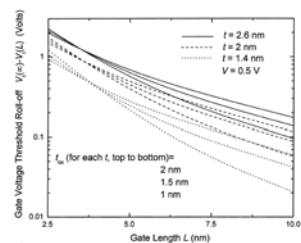
- Transistor critical dimensions
  - Atomic discreteness
  - Subwavelength litho
  - Etch/polish rates
  - Focus
- Number of dopants
- Dopant Placement

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## Parameter Variation

$$I_{ds} = \left( \frac{\mu C_{OX}}{2} \right) \left( \frac{W}{L} \right) (V_{gs} - V_{th})^2$$

- Parameters will vary from device-to-device on the die
  - Include transistor threshold ( $V_{th}$ )



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## ITRS 2005 Variation

Table 18a Design-for-Manufacturability—Near-term Years

Year of Production	2005	2006	2007	2008	2009	2010	2011	2012	2013	Driver
DRAM ½ Pitch (nm) (contacted)	80	70	65	37	50	45	49	36	32	
Mask cost (\$m)	1.5	2.2	3.0	4.5	6.0	9.0	12.0	18.0	24.0	SOC
% $V_{th}$ Variability	10%	10%	10%	10%	10%	10%	10%	10%	10%	SOC
% $V_{th}$ Drift										

Table 18b Design-for-Manufacturability—Long-term Years

Year of Production	2014	2015	2016	2017	2018	2019	2020	Driver
DRAM ½ Pitch (nm) (contacted)	28	25	22	20	18	16	14	
Mask cost (\$m)	36.0	48.0	72.0	96.0	144.0	192.0	288.0	SOC
% CD (nm)								
% $V_{th}$ Variability	10%	10%	10%	10%	10%	10%	10%	SOC
% $V_{th}$ Variability seen at on-chip circuits	81%	81%	81%	81%	112%	112%	112%	SOC
% $V_{th}$ Variability	81%	81%	81%	81%	112%	112%	112%	SOC
% $V_{th}$ Variability	81%	81%	81%	81%	112%	112%	112%	SOC
% Circuit Variability	10%	10%	10%	10%	10%	10%	10%	SOC
% circuit performance variability	50%	61%	62%	65%	66%	69%	69%	SOC
% circuit power variability	50%	60%	60%	61%	61%	62%	62%	SOC
% circuit variability	50%	60%	60%	61%	61%	62%	62%	SOC

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## Scale of Variations

### Die-to-Die (D2D) Variations

#### Systematic

#### (Uncorrelated) Random

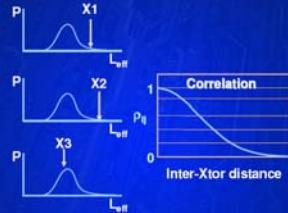
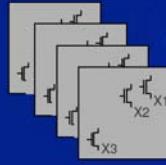


Source: Noel Menezes, Intel ISPD2007

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## Nature of correlated variation



- CDs of transistors that are close track
  - Tracking diminishes with distance

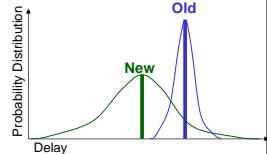
Source: Noel Menezes, Intel ISPD2007

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## Worst Case

- Margins growing due to increasing variation
- Delay=Mean+3 $\sigma$  > older technology?



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## Sequential Paths

- $T_{\text{path}} = t_0 + t_1 + t_2 + t_3 + \dots + t_{(d-1)}$
- $T_i$  – iid random variables
  - Mean  $\tau$
  - Variance  $\sigma$
- $T_{\text{path}}$ 
  - Mean  $d\tau$
  - Variance =  $\sqrt{d} \times \sigma$

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## Sequential Paths

- $T_{\text{path}} = t_0 + t_1 + t_2 + t_3 + \dots + t_{(d-1)}$
- $T_{\text{path}}$ 
  - Mean  $d\tau$
  - Variance =  $\sqrt{d} \times \sigma$
- 3 sigma delay on path:  $d\tau + 3\sqrt{d} \times \sigma$ 
  - Worst case per component would be:  $d\tau + 3\sigma$
  - Overestimate  $d$  vs.  $\sqrt{d}$

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## Parallel Paths

- $T_{\text{cycle}} = \max(T_{p0}, T_{p1}, T_{p2}, \dots, T_{p(n-1)})$
- $P(T_{\text{cycle}} < T_0) = P(T_{p0} < T_0) \times P(T_{p1} < T_0) \times \dots \times P(T_{p(n-1)} < T_0)$ 
  - =  $[P(T_p < T_0)]^n$
- $0.5 = [P(T_p < T_{50})]^n$
- $P(T_p < T_{50}) = (0.5)^{(1/n)}$

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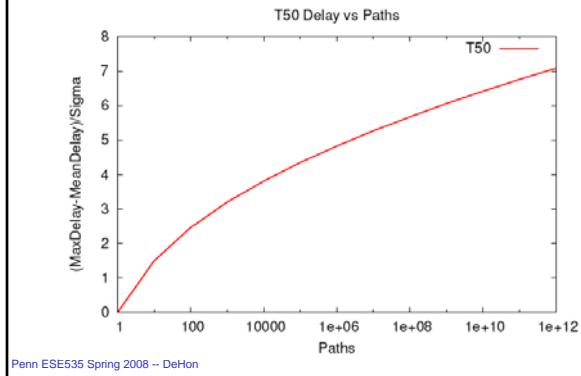
## System Delay

- $P(T_p < T_{50}) = (0.5)^{(1/n)}$ 
  - $N=10^8 \rightarrow 0.999999993$ 
    - $1-7 \times 10^{-9}$
  - $N=10^{10} \rightarrow 0.99999999993$ 
    - $1-7 \times 10^{-11}$
- For 50% yield want
  - 6 to 7  $\sigma$
  - $T_{50} = T_{\text{mean}} + 7\sigma_{\text{path}}$

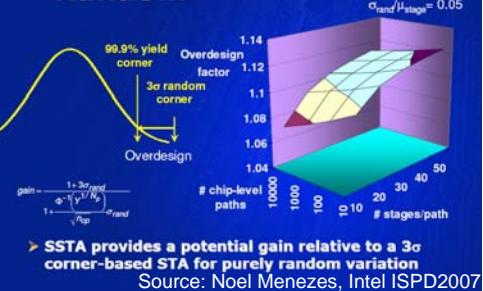
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## System Delay



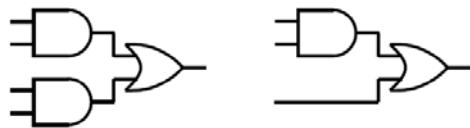
## SSTA gain relative to 3 $\sigma$ corner analysis: Random



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## But does it mislead?

- STA with worst-case says these are equivalent:



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## What do we need to do?

- Ideal:
  - compute PDF for delay at each gate
  - Compute delay of a gate as a PDF from:
    - PDF of inputs
    - PDF of gate delay

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## Delay Calculation Day 7

### AND rules

$i_1 \rightarrow$	0	1	2
$i_2 \downarrow$	0	0	0
0	$MIN(l_1, l_2) + d$	$l_2 + d$	$MIN(l_1, l_2) + d$
1	$MIN(u_1, u_2) + d$	$u_2 + d$	$u_2 + d$
1	0	1	2
	$l_1 + d$	$MAX(l_1, l_2) + d$	$l_1 + d$
	$u_1 + d$	$MAX(u_1, u_2) + d$	$MAX(u_1, u_2) + d$
2	0	2	2
	$MIN(l_1, l_2) + d$	$l_2 + d$	$MIN(l_1, l_2) + d$
	$u_1 + d$	$MAX(u_1, u_2) + d$	$MAX(u_1, u_2) + d$

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## What do we need to do?

- Ideal:
  - compute PDF for delay at each gate
  - Compute delay of a gate as a PDF from:
    - PDF of inputs
    - PDF of gate delay
  - Need to compute for distributions
    - SUM
    - MAX (maybe min)

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## Dealing with PDFs

- Simple model assume all PDFs are Gaussian
  - Model with mean,  $\sigma$
  - Imperfect
    - Not all phenomena are Gaussian
    - Sum of Gaussians is Gaussian
    - Max of Gaussians...is not...

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## Sum of Gaussians

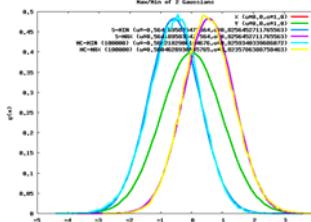
- Two Gaussians
  - $A, \sigma_A$  and  $B, \sigma_B$
  - $SUM = (A+B), \sqrt{\sigma_A^2 + \sigma_B^2}$
- If identical
  - $SUM = 2A, \sigma_A\sqrt{2}$

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## MAX of Two Identical Gaussians

- Given two identical Gaussians A and B with  $\mu$  and  $\sigma$
- Plug into equations
- $E[\text{MAX}(A,B)] = \mu + \sigma/(\pi)^{1/2}$
- $\text{VAR}[\text{MAX}(A,B)] = \sigma^2 - \sigma/\pi$



[Source: Nikil Mehta]

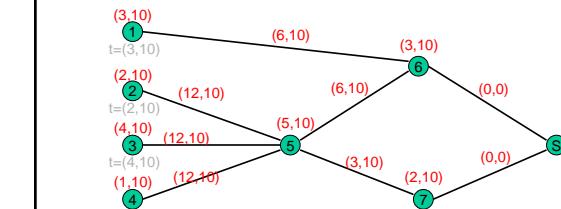
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[Source: Nikil Mehta]

## SSTA Example

- Represent **delay** and arrival time statistically  $(\mu, \sigma)$
- Picking large variance (10) for all delays



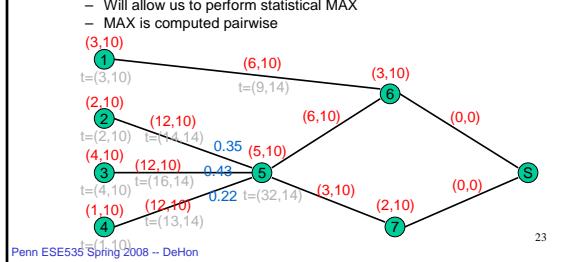
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[Source: Nikil Mehta]

## SSTA Example

- Perform statistical SUM's
- Once we get to node 5, calculate **tightness probabilities** of input edges
  - Will allow us to perform statistical MAX
  - MAX is computed pairwise

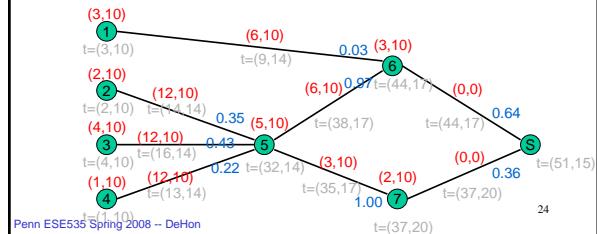


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[Source: Nikil Mehta]

## SSTA Example

- Finish forward pass
  - Now, have statistical delay pdf of circuit
  - Normal distribution with  $\mu=51$  and  $\sigma=15$

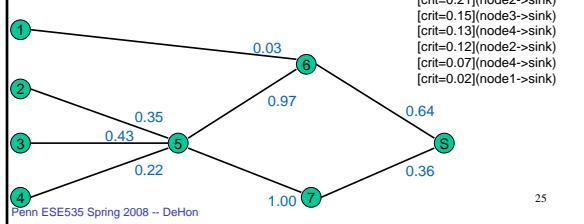


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[Source: Nikil Mehta]

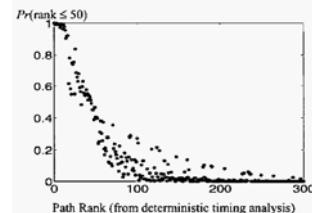
## SSTA Example

- Also have statistical criticality of all paths
  - Criticality = Product of tightness probabilities along path
  - SSTA outputs list of paths in order of criticality
- On backward pass can calculate
  - Statistical slack
  - Statistical node/edge criticality



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## Probability of Path Being Critical



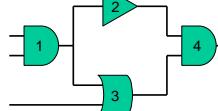
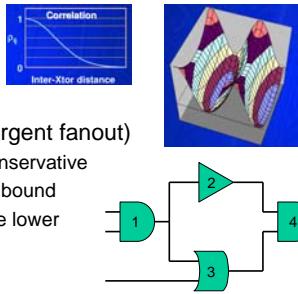
[Source: Intel DAC 2005]

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## More Technicalities

- Correlation
  - Physical on die
  - In path (reconvergent fanout)
    - Makes result conservative
    - Gives upper bound
    - Can compute lower



Graphics from: Noel Menezes (top) and Nikil Mehta (bottom)

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## SSTA vs. Corner Models

- STA with corners predicts 225ps
- SSTA predicts 162ps at 3 $\sigma$
- SSTA reduces pessimism by 28%

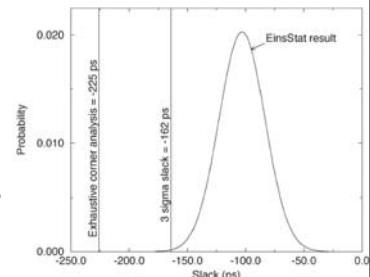


Fig. 11. EinsStat result on industrial ASIC design for early mode slacks.

Source: IBM, TRCAD 2006

## SSTA vs. Monte Carlo Verification Time

- Instead people report SSTA vs Monte Carlo
  - Monte Carlo obviously way slower than just simulating corners
  - However, corners don't cover all cases

[Slide composed  
by Nikil Mehta]

TABLE II  
MONTE CARLO VERSUS EinsStat COMPARISON

Test case	Gates	EinsStat CPU	Monte Carlo	
			Samples	Sequential CPU dd:hh:mm:ss
1	18	1 sec.	100000	5:57
2	3042	2 sec.	100000	2:01:15:10
3	11937	7 sec.	10000	0:20:33:40
4	70216	59 sec.	N/A	4:36:12

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Source: IBM, TRCAD 2006

## Using SSTA in FPGA CAD

[Slide composed  
by Nikil Mehta]

- Le Hei
  - FPGA2007
  - SSTA Synthesis, Place, Route
- Kia
  - FPGA2007
  - Route with SSTA

process variation settings (L2)					
global	5.0%	10.0%	15.0%	20.0%	30.0%
spatial	5.0%	10.0%	15.0%	20.0%	30.0%
local	0.0%	0.0%	0.0%	12.0%	15.0%
total	0.0%	0.0%	0.0%	12.0%	15.0%

deterministic flow					
Tmax (ns)	21.7	22.9	24.4	26.2	28.2
Tavg (ns)	1.8	3.4	5.0	6.4	7.8
Stdev (ns)	-	-	-	-	9.2

stochastic flow					
Tmax (ns)	20.3	21.5	23.4	24.8	26.7
Tavg (ns)	(-0.5%)	(-0.2%)	(+5.8%)	(+5.3%)	(+5.1%)
Stdev (ns)	(-6.4%)	(-7.5%)	(-8.1%)	(-8.2%)	(-8.1%)

Table 6. Comparison of mean delay and standard deviation between deterministic and stochastic flows under various process variation assumptions (based on the geometric mean of 20 MCNC designs).

Circuit	Delay Impr.(%)
ex5ip	6.58
alu4	1.50
misex3	5.76
apex2	3.24
apex4	2.57
pdc	4.74
seq	4.37
des	3.73
phi4	4.82
ext010	2.43
frisc	2.84
elliptic	0.17
bigkey	0.35
s298	7.10
tseng	5.93
difreq	4.16
dsip	7.37
s83417	7.56
s83584.1	5.43
clma	-1.17
Mean	3.95

## Summary

- Nanoscale fabrication is a statistical process
- Delays are PDFs
- Assuming each device is worst-case delay is too pessimistic
  - Wrong prediction about timing
  - Leads optimization in wrong direction
- Reformulate timing analysis as statistical calculation
- Estimate the PDF of circuit delays

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## Admin

- Reading for Monday
- Homework due Monday

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## Big Ideas:

- Coping with uncertainty
- Statistical Reasoning and Calculation

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